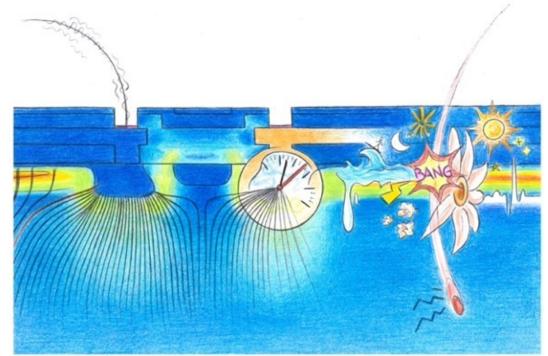
### Topics in LGAD design

- SEB-resistant (Single Event Burn-out) LGAD design
- DC-RSD



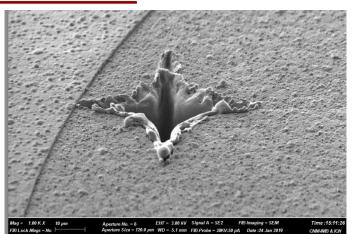
N. Cartiglia 4DInSiDe PRIN

(INFN Torino & Genova, UniTo, UniPO, Univ. of Perugia, CNR-Perugia)

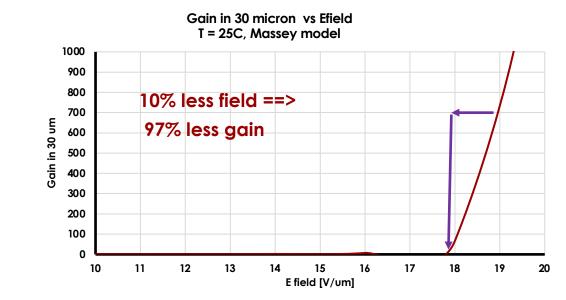
FBK, Univ. of Trento, UCSC

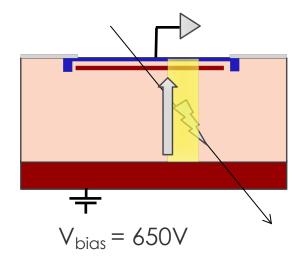
## Part I: SEB-resistant LGAD design

- 50  $\mu$ m thick LGAD sensors exposed to 120 GeV/c protons, when biased at 625V or higher (12.5V/ $\mu$ m), break down permanently.
- 45  $\mu$ m thick LGAD broke down at 550V (12.2V/ $\mu$ m)
- 50 μm thick LGAD sensors, biased at 575V or less (11.5V/μm), did not break.
- 55  $\mu$ m thick LGAD survived many hours at 600V (10.9V/ $\mu$ m).

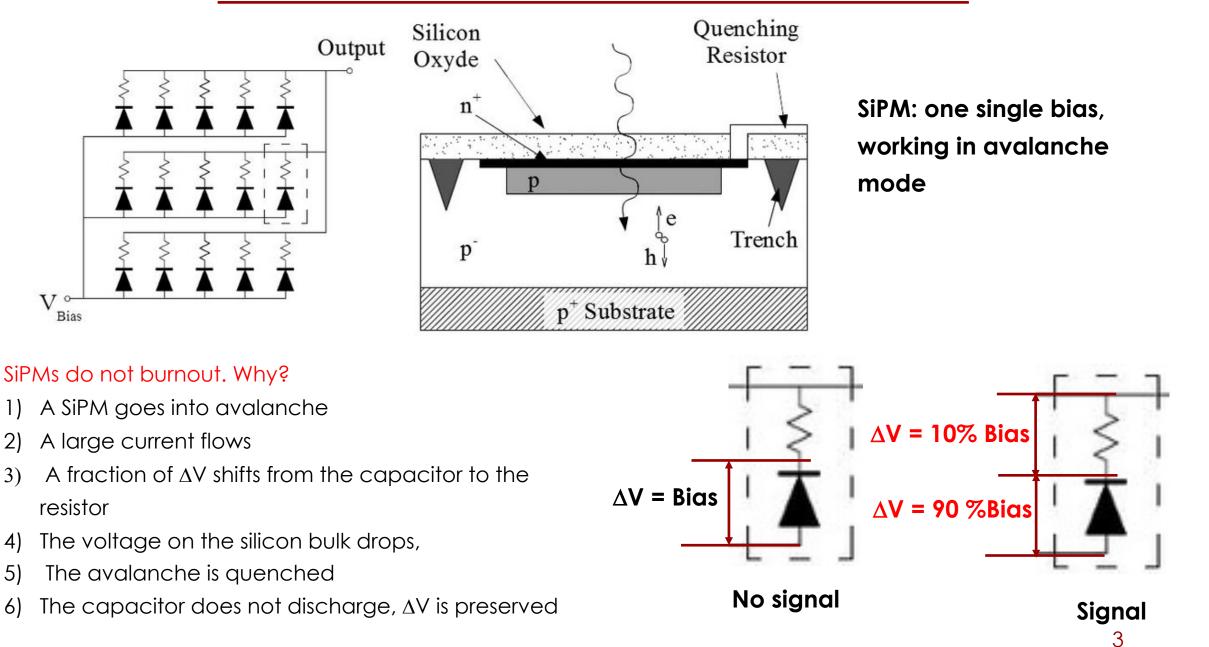


#### Threshold effect: SEBs happen quickly if the Electric field is high enough





# SiPM: aide mémoire



2)

3)

4)

5)

6)

Bias

resistor

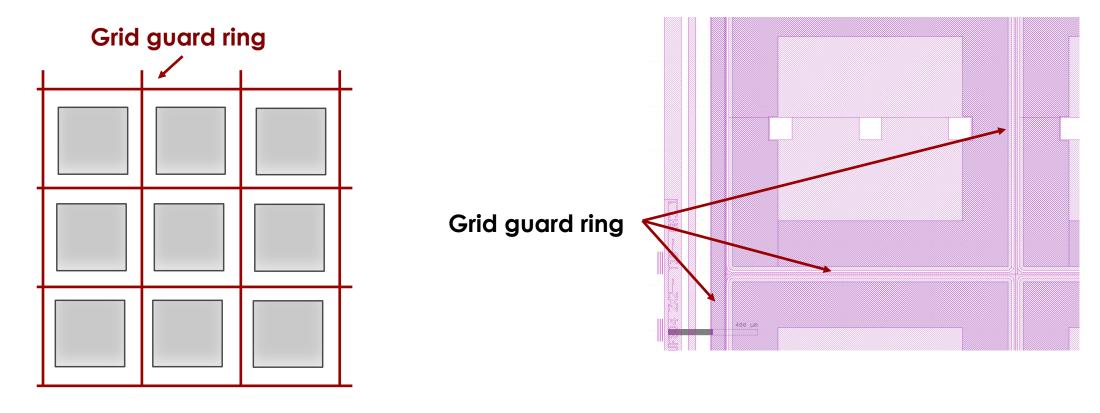
### SEB-resistant LGAD design

Can we add a quenching resistor in LGAD? What are the consequences?

- Where do we connect the resistors to ground?
- Do we spoil the signal shape?
- Do we increase dramatically the fill factor?
- How do we do this study?

# LGAD matrix with grid guard-ring

Independently from the SEB issue, FBK has developed LGAD matrices with a grid guardring, i.e., there is a ground grid among the pads (the so-called FBK UFSD Type10)



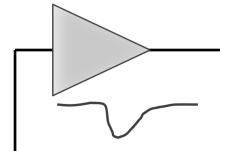
No-gain region ~ 70 um

We have a design where each pad has a near-by ground. Can we use it?

## LGAD: aide mémoire

#### Signal formation:

- The signal is formed on the n++
- It is AC-coupled to the metal
  - ==> that is why the timing is not "position dependent" as it is in "not metallized" LGADs.
- Charges travels along the n++
- The signal on the metal and the charges on the n++ combines
  => that is why the signal is unipolar and not bi-polar



#### Oddly, the LGAD read-out is a mixture of AC- and DC-modes

